

## Silicon NPN Power Transistors

BUL510

## DESCRIPTION

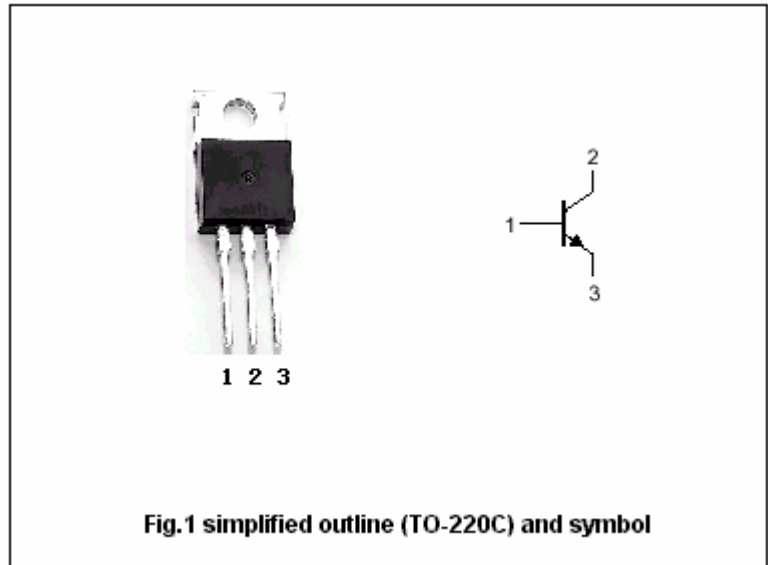
- With TO-220C package
- High voltage,high speed

## APPLICATIONS

- Electronic ballasts for fluorescent lighting
- Switch mode power supplies
- Electronic transformer for halogen lamp

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1000	V
$V_{CEO}$	Collector-emitter voltage	Open base	450	V
$V_{EBO}$	Emitter-base voltage	Open collector	9	V
$I_C$	Collector current (DC)		10	A
$I_{CM}$	Collector current-Peak	$t_p < 5\text{ms}$	18	A
$I_B$	Base current (DC)		3.5	A
$I_{BM}$	Base current-Peak	$t_p < 5\text{ms}$	7	A
$P_{tot}$	Total power dissipation	$T_C=25^\circ\text{C}$	100	W
$T_j$	Maximum operating junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-65~150	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-case}}$	Thermal resistance junction to case	1.25	$^\circ\text{C}/\text{W}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0; L=25mH	450			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10mA ; I <sub>C</sub> =0	9			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.6A			0.8	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.8A			1.0	V
V <sub>CEsat-3</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1.25A			1.5	V
V <sub>BEsat-1</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A ; I <sub>B</sub> =0.6A			1.2	V
V <sub>BEsat-2</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =1.25A			1.5	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =1000V; V <sub>BE</sub> =0 T <sub>C</sub> =125°C			100 500	μA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =450V; I <sub>B</sub> =0			250	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	15		45	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =10mA ; V <sub>CE</sub> =5V	10			

## Switching times inductive load

t <sub>s</sub>	Storage time	I <sub>C</sub> =4A ; V <sub>CL</sub> =300V I <sub>B1</sub> =0.8A; I <sub>B2</sub> =-1.6A L=200μH			3.4	μs
t <sub>f</sub>	Fall time				0.15	μs

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PACKAGE OUTLINE

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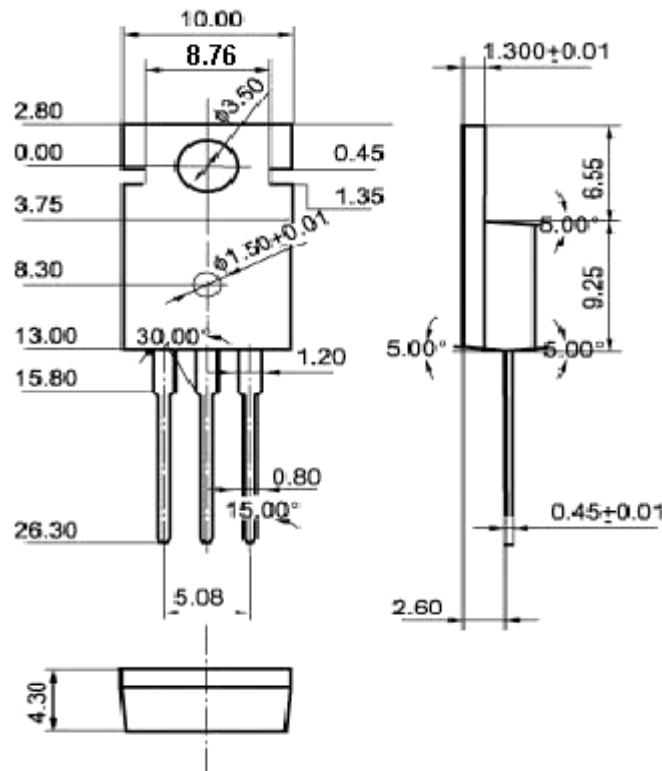


Fig.2 Outline dimensions (unindicated tolerance: 0.1mm)